TOSHIBA Thyristor Silicon Planar Type

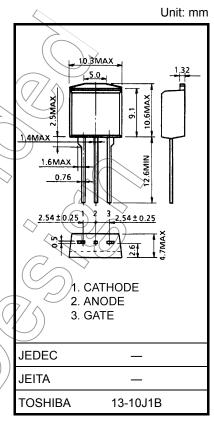
S6A13

Condenser Discharge Control Applications

- FWD included between cathode and anode
- Critical rate of rise of ON-state current: di/dt = 750 A/µs
- Repetitive peak surge ON-state current: $I_{TRM} = 500 \text{ A} (t_w = 2 \text{ } \mu \text{s})$
- Repetitive peak OFF-state voltage: VDRM = 800 V
- Gate trigger current: I_{GT} = 30 mA (max)

Absolute Maximum Ratings

Characteristics	Symbol	Rating	Unit
Repetitive peak OFF-state voltage	V_{DRM}	800	$\langle \psi \rangle$
Repetitive peak surge ON-state current (Note 1)	I _{TRM}	500	A
Repetitive peak surge forward current (Note 1)	I _{FRM}	500	A
Critical rate of rise of ON-state current (Note 1)	di/dt	750	A/μs
Peak gate power dissipation	P _{GM}	5	/_(W
Average gate power dissipation	P _G (AV)	0.5	W
Peak forward gate voltage	V _{FGM})) 10	V
Peak reverse gate voltage	VRGM	-5 ^{<}	\ v
Peak forward gate current	1 _{GM}	2	ZA
Junction temperature	$7/\sqrt{T_j}$	-40~125	∫ °C
Storage temperature range	T _{stg}	-40~150	→°C
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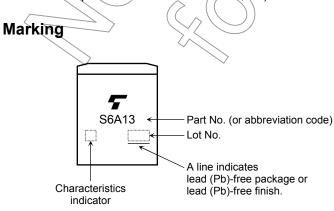


Weight: 1.5 g (typ.)

Note 1: $V_D \le 0.8 \times \text{rated}$, $T_C = 85^{\circ}C$, $i_{gp} \ge 60 \text{ mA}$, $t_{gw} \ge 10 \text{ }\mu\text{s}$, $t_{gr} \le 150 \text{ ns}$

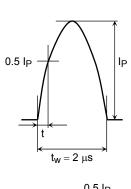
Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



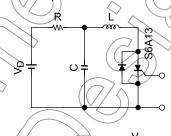
Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Repetitive peak OFF-state current	I _{DRM}	V _{DRM} = Rated	_	_	10	μА
Peak ON-state voltage (thyristor)	V_{TM}	I _{TM} = 25 A	_	_	1.5	V
Peak forward voltage (diode)	V _{FM}	I _{FM} = 25 A	/	_	2.0	V
Gate trigger voltage	V _{GT}	V _D = 6 V, R _I = 10 Ω		_	1.0	V
Gate trigger current	I _{GT}	V[) = 0 V, [] = 10 22	(F) }_	30	mA
Gate non-trigger voltage	V_{GD}	V _D = Rated, Tc = 125°C	0.2	_	_	V
Critical rate of rise of OFF-state voltage	dv/dt	V _{DRM} = Rated, Tc = 125°C Exponential Rise	9)	50	_	V/μs
Holding current	lΗ	V _D = 6 V, I _{TM} = 1 A	_	_	35	mA
Thermal resistance (junction to ambient)	R _{th (j-a)}	DC	_		70	°C/W



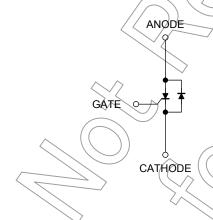
 $di/dt = \frac{0.5 \text{ Ip}}{t}$



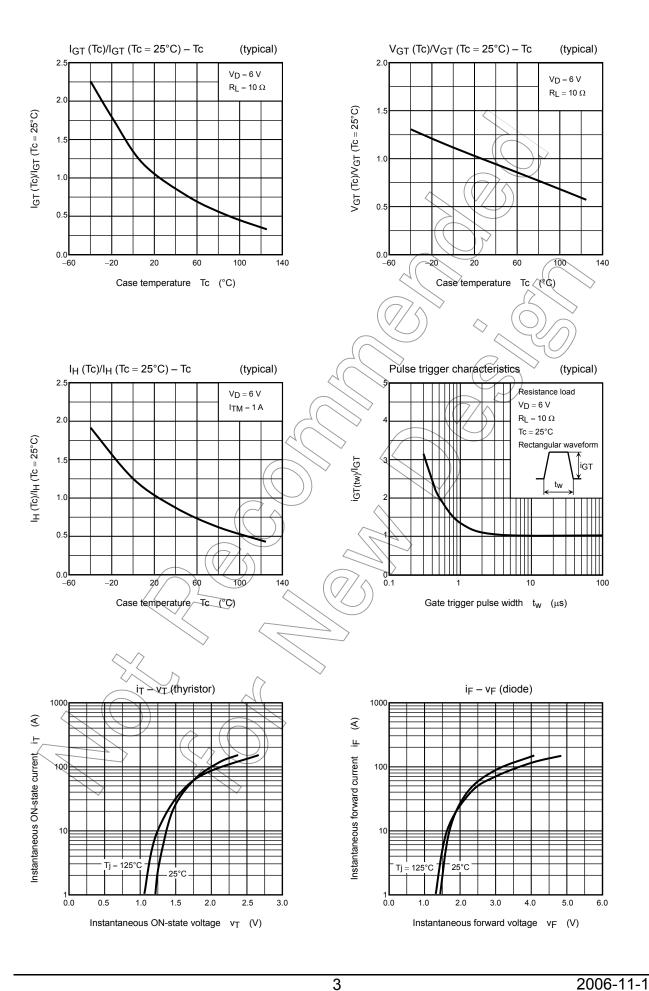


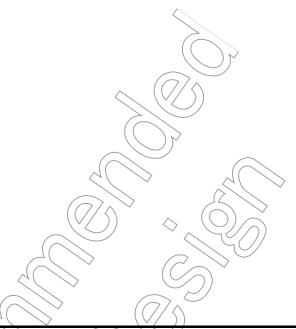
$$t_W = \pi \sqrt{LC}$$
, $I_P = \frac{V_D}{\sqrt{L/C}}$

Equivalent Circuit



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